Elektronische Bauelemente

SSM3055L-C

2.8A, 60V, $R_{DS(ON)}$ 100 mΩ
N-Channel Enhancement Mode MOSFET

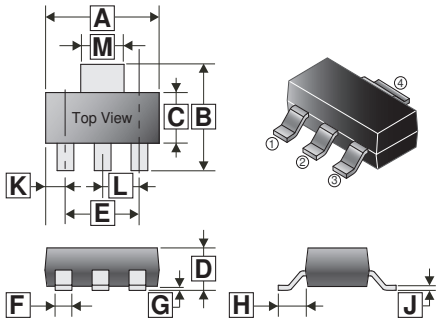
RoHS Compliant Product
A suffix of "-C" specifies halogen and lead-free

DESCRIPTION

The SSM3055L-C utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The SSM3055L-C is universally used for all commercial-industrial applications.

SOT-223

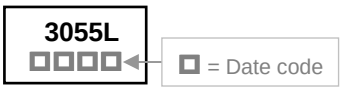


REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	5.90	6.70	G	-	0.18
B	6.70	7.30	H	2.00 REF.	
C	3.30	3.80	J	0.20	0.40
D	1.42	1.90	K	1.10 REF.	
E	4.45	4.75	L	2.30 REF.	
F	0.60	0.85	M	2.80	3.20

FEATURES

- Simple Drive Requirement
- Small Package Outline

MARKING

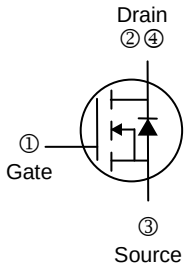


PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-223	2.5K	13 inch

ORDER INFORMATION

Part Number	Type
SSM3055L-C	Lead (Pb)-free and Halogen-free



ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [1], V_{GS}@10V	T_A=25℃	I_D	2.8	A
	T_A=70℃		2.3	
Pulsed Drain Current [2]		I_{DM}	12	A
Power Dissipation [3]	T_A=25℃	P_D	1.5	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	℃
Thermal Resistance Ratings				
Maximum Junction to Ambient [1]		$R_{\theta JA}$	85	℃/W
Maximum Junction to Case [1]		$R_{\theta JC}$	48	℃/W

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage		BV_{DSS}	60	-	-	V	V_{GS}=0, I_D=250μA
Gate-Threshold Voltage		$V_{GS(th)}$	1	-	2.5	V	V_{DS}=V_{GS}, I_D=250μA
Gate-Body Leakage Current		I_{GSS}	-	-	±100	nA	V_{GS}= ±20V
Drain-Source Leakage Current	T_J=25℃	I_{DSS}	-	-	1	μA	V_{DS}=48V, V_{GS}=0
	T_J=55℃		-	-	5		V_{DS}=48V, V_{GS}=0
Drain-Source On-Resistance [2]		$R_{DS(ON)}$	-	-	100	mΩ	V_{GS}=10V, I_D=2.5A
			-	-	110		V_{GS}=4.5V, I_D=2A
Total Gate Charge		Q_g	-	5	-	nC	V_{DS}=48V V_{GS}=4.5V I_D=2A
Gate-Source Charge		Q_{gs}	-	1.68	-		
Gate-Drain (''Miller'') Charge		Q_{gd}	-	1.9	-		
Turn-on Delay Time [2]		$T_{d(on)}$	-	1.6	-	nS	V_{DD}=30V V_{GS}=10V R_G=3.3Ω I_D=2A
Rise Time		T_r	-	7.2	-		
Turn-off Delay Time		$T_{d(off)}$	-	25	-		
Fall Time		T_f	-	14.4	-		
Input Capacitance		C_{iss}	-	511	-	pF	V_{GS}=0 V_{DS}=15V f=1.0MHz
Output Capacitance		C_{oss}	-	38	-		
Reverse Transfer Capacitance		C_{rss}	-	25	-		
Source-Drain Diode							
Diode Forward Voltage [2]		V_{SD}	-	-	1.2	V	I_S=1A, V_{GS}=0
Continuous Source Current [1.4]		I_S	-	-	2.8	A	V_G=V_D=0, Force Current
Pulsed Source Current [2.4]		I_{SM}	-	-	12		
Reverse Recovery Time		T_{RR}	-	9.7	-	nS	I_S=2A, dI/dt=100A/μs V_{GS}=0
Reverse Recovery Charge		Q_{RR}	-	5.8	-	nC	

Notes:
1. Surface mounted on a 1 inch^2 FR4 board with 2OZ copper, t≦10sec., 125℃/W when mounted on Min. copper pad.
2. The data tested by pulsed, pulse width≦300μs, duty cycle≦2%.
3. The power dissipation is limited by 150℃ junct ion temperature.
4. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

CHARACTERISTIC CURVES

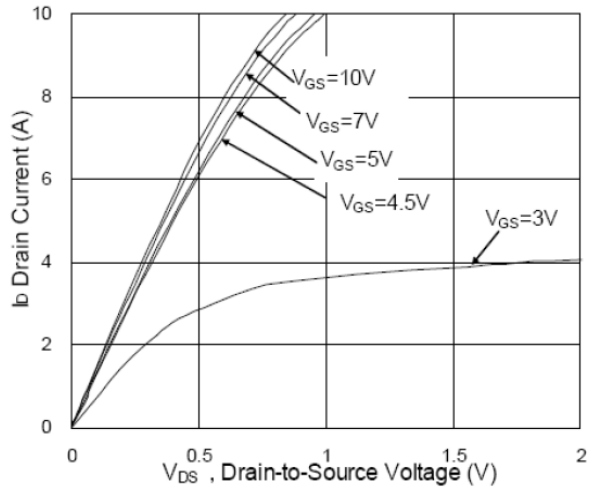


Fig.1 Typical Output Characteristics

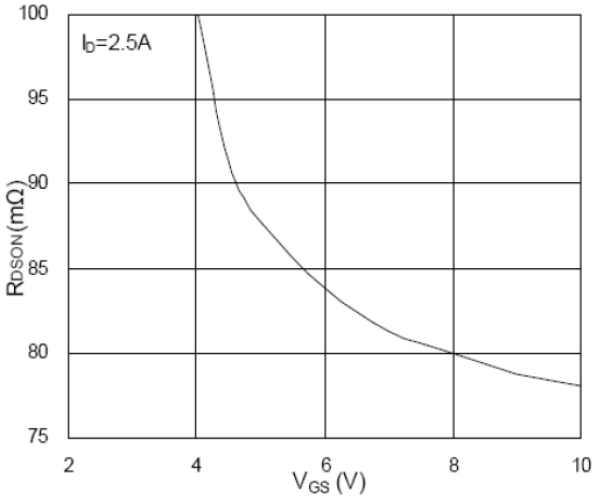


Fig.2 On-Resistance v.s Gate-Source

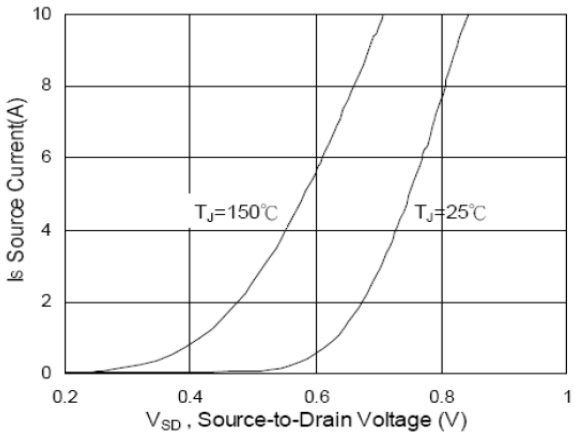


Fig.3 Forward Characteristics of Reverse

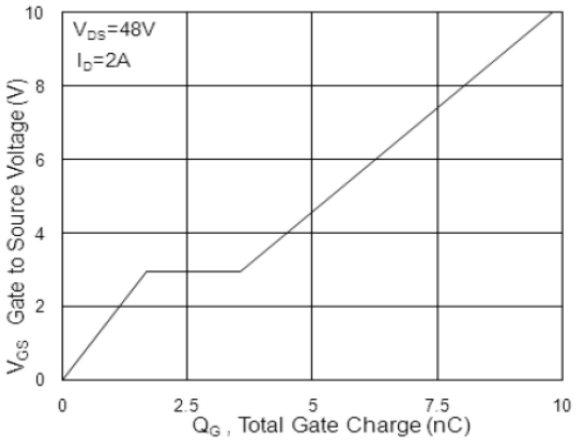


Fig.4 Gate-Charge Characteristics

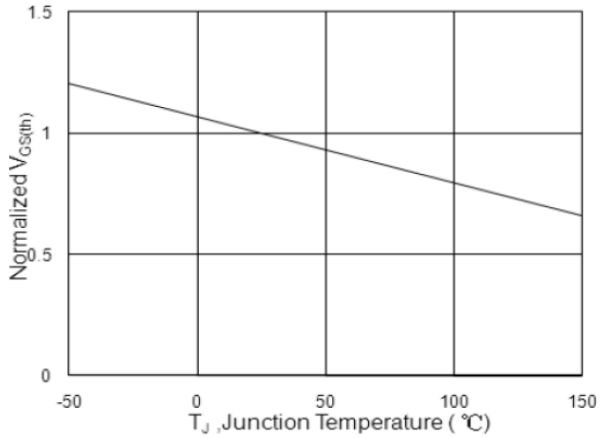


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

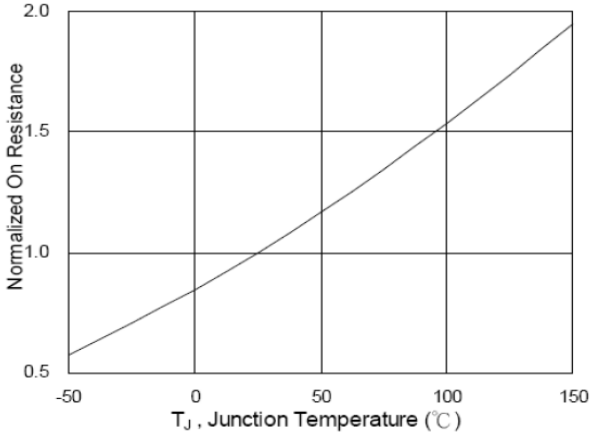


Fig.6 Normalized R_{DSON} v.s T_J

CHARACTERISTIC CURVES

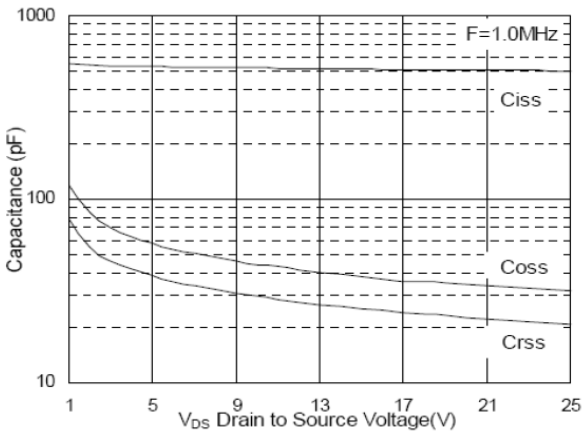


Fig.7 Capacitance

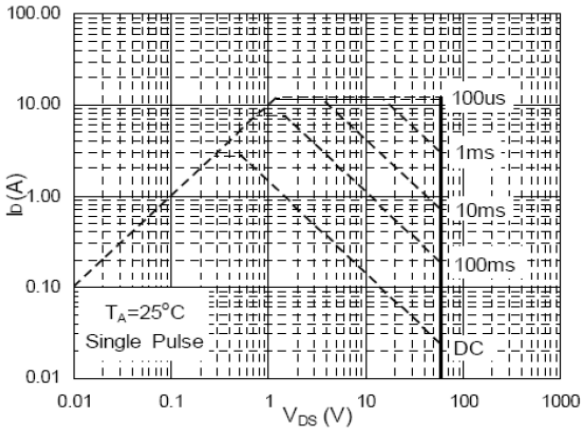


Fig.8 Safe Operating Area

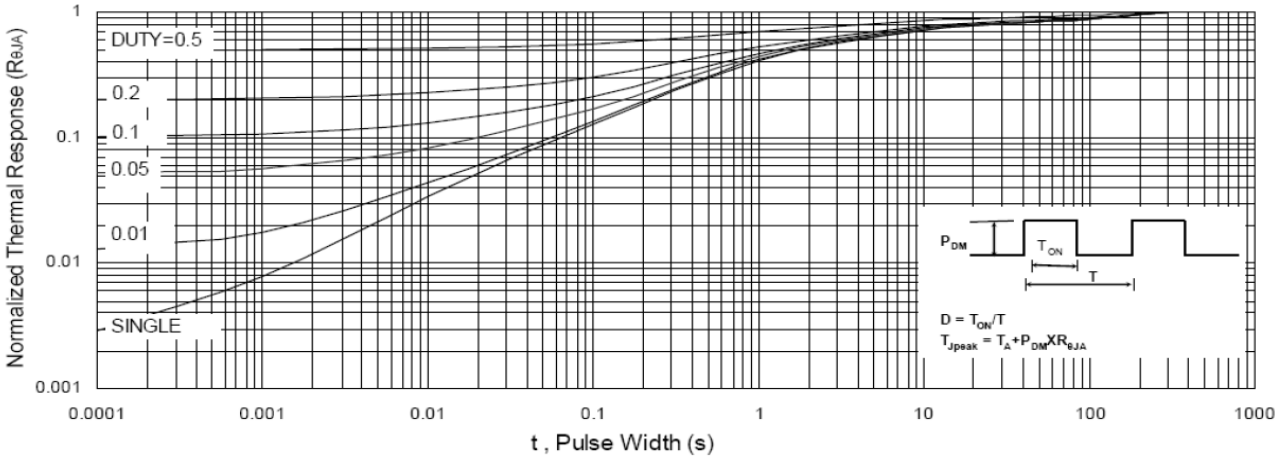


Fig.9 Normalized Maximum Transient Thermal Impedance

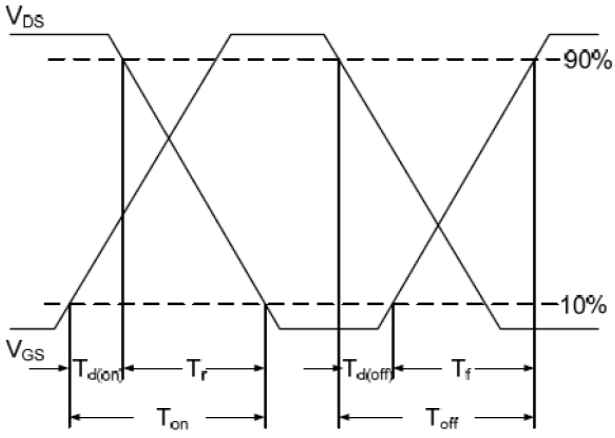


Fig.10 Switching Time Waveform

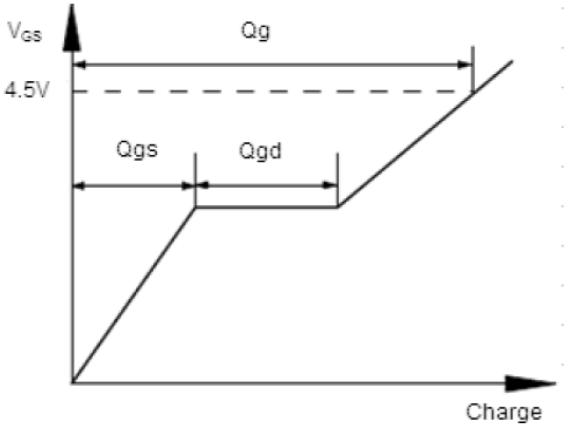


Fig.11 Gate Charge Waveform